

Dual Serise Switching Diodes

FEATURES

- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- Pb-Free package is available.

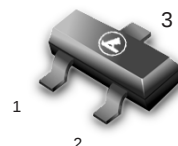
DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LDAN202UT1	N	3000/Tape&Reel
LDAN202UT1G (Pb-Free)	N	3000/Tape&Reel

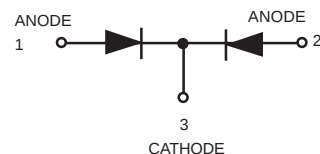
MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Forward Current	I_o	100	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	300	mAdc
Forward voltage($I_f = 100mA$)	V_F	1.2	V
Reverse current($V_r = 70V$)	I_R	0.1	uA
Capacitance between terminals($f = 1MHz$)	C_T	3.5	pF
Reverse recovery time($V_r = 6V, I_f = 5mA$)	T_{rr}	4	nS

LDAN202UT1



SOT-323/SC-70



ELECTRICAL CHARACTERISTIC CURVES

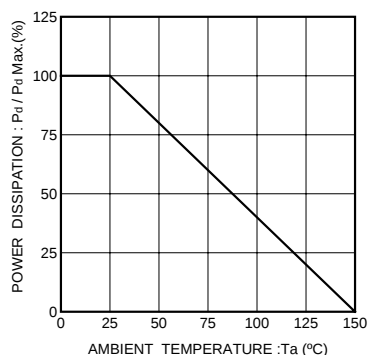


Fig.1 Power attenuation curve

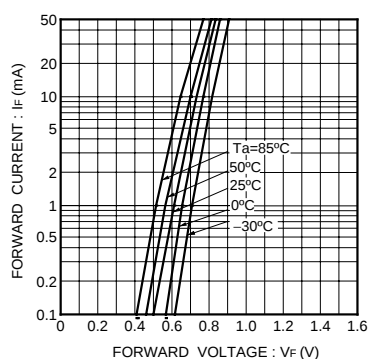


Fig.2 Forward characteristics (P Type)

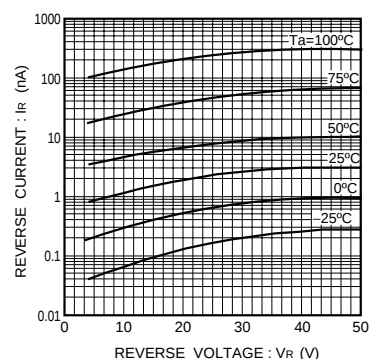


Fig.3 Reverse characteristics (P Type)

LDAN202UT1

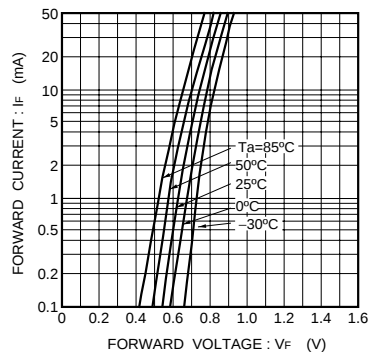


Fig.4 Forward characteristics (N Type)

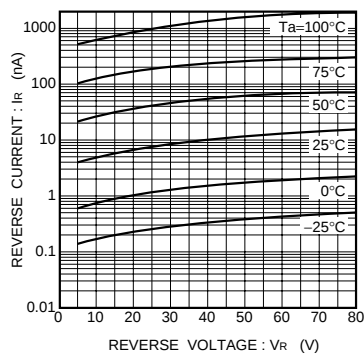


Fig.5 Reverse characteristics (N Type)

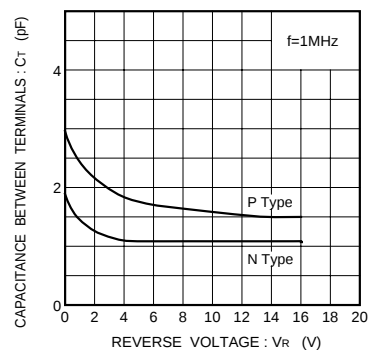


Fig.6 Capacitance between terminals characteristics

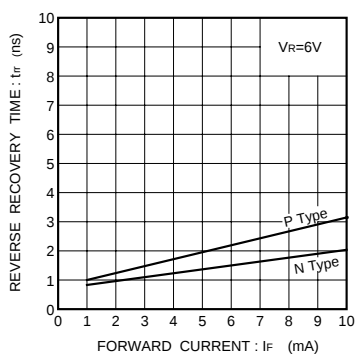


Fig.7 Reverse recovery time

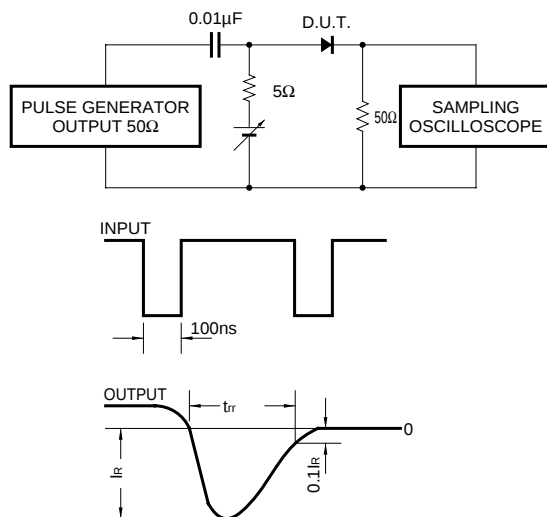


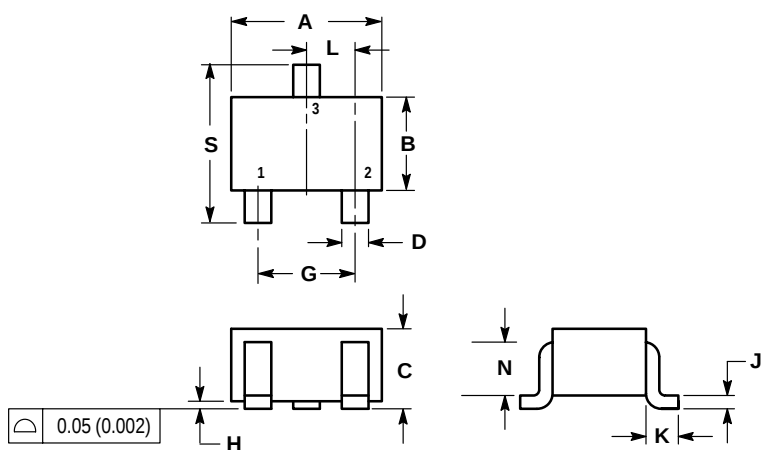
Fig.8 Reverse recovery time (t_{rr}) measurement circuit

LDAN202UT1

SC-70 / SOT-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

